

Electromagnetically induced transparency and wide-band wavelength conversion in silicon nitride microdisk optomechanical resonators

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We demonstrate optomechanically-mediated electromagnetically-induced transparency and wavelength conversion in silicon nitride (Si_3N_4) microdisk resonators. Fabricated devices support whispering gallery optical modes with a quality factor (Q) of 10^6 , and radial breathing mechanical modes with a $Q=10^4$ and a resonance frequency of 625 MHz, so that the system is in the resolved sideband regime. Placing a strong optical control field on the red (blue) detuned sideband of the optical mode produces coherent interference with a resonant probe beam, inducing a transparency (absorption) window for the probe. This is observed for multiple optical modes of the device, all of which couple to the same mechanical mode, and which can be widely separated in wavelength due to the large bandgap of Si_3N_4 . These properties are exploited to demonstrate frequency upconversion and downconversion of optical signals between the 1300 nm and 980 nm bands.

Recent demonstrations of strong radiation pressure interactions in cavity optomechanics have focused on the resolved sideband regime, where mechanical sidebands of the optical mode lie outside its linewidth [1]. Such systems have been used in laser cooling of a mechanical oscillator to its ground state [2, 3], coherent interference effects such as electromagnetically-induced transparency and absorption [4, 5], parametrically-driven normal mode splitting [6–8], and observing energy exchange between the optical and mechanical systems [8, 9]. In the context of chip-based micro- and nanophotonic devices, silica microtoroid cavities [4, 8] and silicon photonic/phononic crystal resonators (optomechanical crystals) [3, 5, 10] are two successful systems that exhibit significantly different parameter regimes. Silica microtoroids typically support ultra-high quality factor optical modes ($Q_o > 10^7$, decay rate $\kappa/2\pi \approx 10$ MHz) that are coupled to $\gtrsim 50$ MHz frequency mechanical modes with a zero-point optomechanical coupling rate $g_0/2\pi \gtrsim 1$ kHz. In contrast, silicon optomechanical crystals have $Q_o \approx 10^6$ ($\kappa/2\pi \gtrsim 200$ MHz) modes that couple to few GHz mechanical modes with $g_0/2\pi \approx 1$ MHz.

Here, we consider a chip-scale platform formed by silicon nitride (Si_3N_4) microdisks, in which $Q_o \approx 10^6$ modes couple to a 625 MHz mechanical radial breathing mode with $g_0/2\pi \approx 8$ kHz. This sideband-resolved device combines some advantageous features of the aforementioned systems, such as high mechanical frequency, a straightforward optical mode structure with multiple high- Q modes coupled to the same mechanical mode, and operation in a material whose broad transparency and low nonlinear loss enables large intracavity photon numbers to be achieved over a range of wavelengths. We demonstrate optomechanically-mediated electromagnetically induced transparency (EIT) and wavelength conversion [11–14], up- and downconverting signals between the 1300 nm and

980 nm wavelength bands. We note the qualitative difference with respect to previous studies using microdisk optomechanical resonators, which focused on topics like sensitive optical transduction of motion [15], including at GHz frequencies [16], mechanical oscillation and cooling [17], and optical mode tuning [18].

Microdisks are fabricated in 350 nm thick Si_3N_4 -on-silicon, as described in the Supplementary Material [19]. Similar Si_3N_4 microdisks have exhibited $\kappa/2\pi \gtrsim 100$ MHz [20], so that a 10 μm disk diameter was chosen since it is small enough to place the mechanical radial breathing mode (RBM) frequency above the anticipated κ , and large enough to avoid optical radiation loss due to imperfect total internal reflection. Finite element method simulations of the mechanical modes further inform our choice of geometry [19]. Low mechanical dissipation requires the coupling between the breathing mode and lossy modes of the supporting silicon pedestal to be minimized. Assuming a conical frustum for the pedestal shape, we calculate mechanical modes as a function of pedestal radius at the interface with Si_3N_4 (Fig. 1(e)), with displacement amplitude profiles shown for two modes at a radius of 500 nm. We also plot the mechanical mode frequencies and Q s due to clamping losses, following the approach of Anetsberger et al. [21]. We find that the pedestal radius should shrink to $\lesssim 100$ nm to achieve optimum Q ; in practice, we have been able to achieve values of about 100 nm, where the theoretical value is $Q \approx 4 \times 10^4$.

We first characterize basic optical and mechanical properties of the system (Fig. 1(a)). Light is coupled to the devices using an optical fiber taper waveguide (FTW), and optical modes are measured by sweeping a 1300 nm or 980 nm band tunable diode laser and recording the transmitted signal through the FTW on a 1 MHz bandwidth photodetector. In the 1300 nm band, only transverse electric (TE) polarized modes are observed,

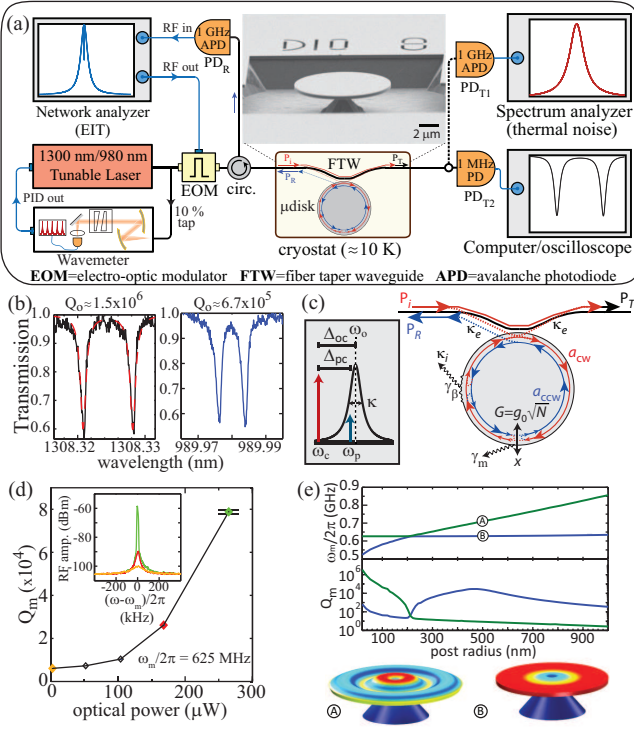


FIG. 1. (a) Measurement setup and scanning electron micrograph of a representative device. (b) Room-temperature 1300 nm and 980 nm band optical modes. (c) Schematic of sideband spectroscopy and the microdisk. a_{cw}/a_{ccw} are amplitudes for clockwise/counterclockwise (cw/ccw) optical modes, which couple to the radial breathing mode (amplitude x) at a rate g_0 that is parametrically-enhanced to a rate G through a control field that injects N photons into the cavity. κ_i and κ_e are the intrinsic loss and waveguide-cavity coupling rates, respectively, γ_m is the mechanical damping rate, and γ_β is a backscattering rate that couples the cw/ccw modes. $P_i/P_R/P_T$ are the incident, reflected, and transmitted powers through the FTW. (d) Room-temperature mechanical Q as a function of input optical power (laser blue-detuned from the optical mode) for the radial breathing mode. The inset shows the mechanical mode spectrum at the three highlighted optical powers. Error bars are from the 95 % confidence intervals in Lorentzian fits of the spectra [19]. (e) Finite-element-method calculated frequency (top) and mechanical Q (middle) for two modes, labeled A and B, as a function of top pedestal radius. The modes anti-cross at a radius of 200 nm. (bottom) Displacement profiles for a radius of 500 nm.

while in the 980 nm band, both TE and TM (transverse magnetic) modes are seen. Mechanical modes are measured at low optical power ($\approx 0.2 \mu W$) by tuning the laser wavelength to the shoulder of an optical mode, so that the fluctuating optical mode wavelength induced by thermal-noise-driven mechanical motion is converted to intensity modulation [1]. This optical signal is detected with a 1 GHz bandwidth avalanche photodiode (APD) and resolved on a real-time electronic spectrum analyzer. At room temperature and under moderate vacuum ($0.002 \text{ Pa} \approx 2 \times 10^{-5} \text{ torr}$), Q_o as high as 2×10^6 at both 1300 nm and 980 nm are measured, on par with pre-

vious work on Si_3N_4 microdisks [20]. Figure 1(b) shows a representative scan for the device we focus on, whose total (intrinsic) Q_o is 1.5×10^6 (1.7×10^6) at 1308 nm, and 6.7×10^5 (7.6×10^5) at 990 nm. While many mechanical modes are observed, we focus on the fundamental radial breathing mode at $\omega_m/2\pi \approx 625 \text{ MHz}$, whose mechanical Q (Q_m) is 6×10^3 (inset to Fig. 1(d)). Increasing the optical power with the laser blue-detuned with respect to the cavity mode results in a pronounced narrowing of the mechanical mode by over an order of magnitude, as the laser drives the system into regenerative oscillations [1]. On the other hand, strong pumping on the red-detuned side of the cavity is limited by instability due to thermo-optic effects. To improve this, the device is cooled in a liquid He flow cryostat to $\approx 10 \text{ K}$. Generally, we see an increase in the undriven Q_m , to 1×10^4 , and some degradation of Q_o (by as much as a factor of 3), which we attribute to cryo-gettering of material on the sample. The splitting in the doublet mode optical transmission spectra, produced by backscattering that couples the traveling wave modes of the disk into frequency-split standing wave modes [22], also changes. These changes vary from cooldown to cooldown.

In the context of cavity optomechanics, EIT is an increase in the transmission of a near-resonant probe beam (frequency ω_p) through an optical cavity (at ω_o) that results when a strong control field (at ω_c) is red-detuned by $\Delta_{oc} = \omega_o - \omega_c = \omega_m$ (Fig. 1(c)), so that anti-Stokes photons generated by scattering of the control field by the mechanical resonator interfere with the probe and create a transparency window for it [4, 5, 23]. We focus on the reflected signal from the cavity, present in our microdisks due to the aforementioned backscattering, and for which EIT results in a narrow dip in the reflection peak. The probe is derived from the control field using an electro-optic amplitude modulator (EOM) to generate higher and lower frequency sidebands, only one of which is coupled into the cavity since it operates in the resolved sideband limit. The EOM is driven by a network analyzer, with the modulation frequency swept to vary the probe-control beam detuning $\Delta_{pc} = \omega_p - \omega_c$. The probe and control fields pass through a circulator before going to the device, whose reflected signal is demodulated by the network analyzer. A wavemeter tracks the control field wavelength and is used in feedback to lock Δ_{oc} [19].

We first study the system in the 1300 nm band, by sweeping Δ_{pc} at different values of Δ_{oc} . For each Δ_{oc} , we take two sweeps of Δ_{pc} , over a broad range to trace the overall cavity reflection spectrum, and over a narrow range to resolve the narrow EIT dip [19]. A series of spectra is shown in Fig. 2(a), where Q_o has slightly degraded compared to its room temperature value, with $\kappa/2\pi \approx 180 \text{ MHz}$. As observed in previous work [4, 5], the EIT dip always appears at $\Delta_{pc} = \omega_m$, and its width is given by the total mechanical damping rate γ , which is the sum of the intrinsic rate γ_m and the optomechanically-

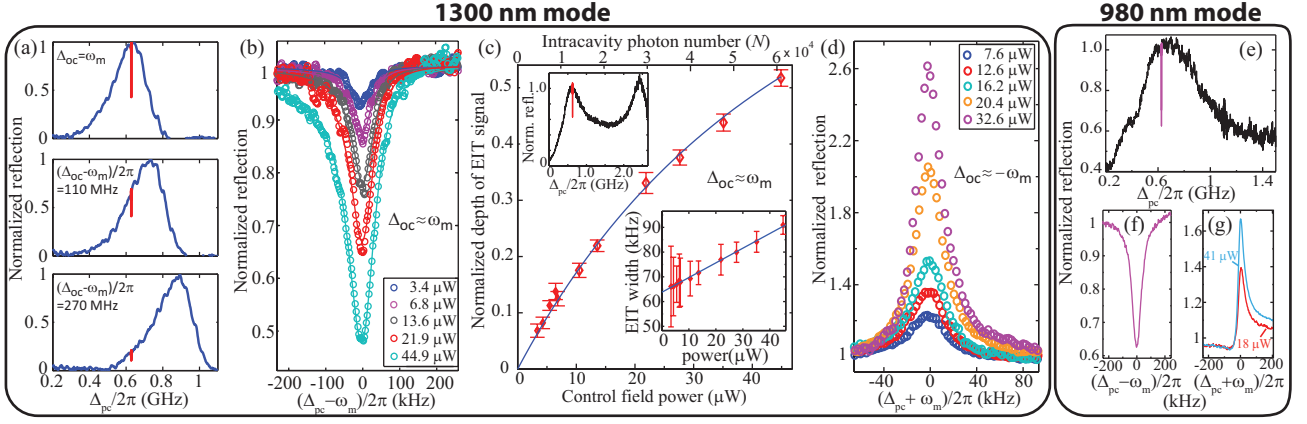


FIG. 2. EIT/EIA measurements for a (a)-(d) 1300 nm and (e)-(g) 980 nm mode. (a) Reflection spectra with the optical mode-control field detuning (Δ_{oc}) stepped and the probe-control detuning (Δ_{pc}) swept. Blue (red) curves are taken over a broad (narrow) range of Δ_{pc} . (b) Zoomed-in reflection spectra (open circles are data, solid lines are fits) and (c) Depth of the EIT dip as a function of control field power, for $\Delta_{oc} \approx \omega_m$. The upper inset shows the broad reflection spectrum corresponding to the data in (b)-(c), for which Q_o had degraded with respect to that in (a). The lower inset shows the width of the EIT dip in (b) as a function of control field power. Determination of the error bars is described in the Supplementary Information. (d) Zoomed-in reflection spectra for $\Delta_{oc} = -\omega_m$, for which EIA is observed. (e) Broad, and (f)-(g) narrow reflection spectra as a function of Δ_{pc} for a cavity mode in the 980 nm band. In (e)-(f), $\Delta_{oc} \approx \omega_m$, while in (g), $\Delta_{oc} \approx -\omega_m$.

induced damping rate $\gamma_{OM} = C\gamma_m$, where C is the cooperativity parameter. $C = \frac{4G^2}{\kappa\gamma_m}$, where $G = g_0\sqrt{N}$ is the parametrically-enhanced coupling rate provided by N intracavity control field photons. We reach $C \approx 0.45$ before the system is thermally unstable.

To more quantitatively understand the EIT effect and assess the zero-point optomechanical coupling rate g_0 , we set $\Delta_{oc} \approx \omega_m$ and measure the normalized reflection spectrum as a function of control field power (Fig. 2(b)). For this set of measurements, Q_o degraded upon cooldown to $\kappa/2\pi \approx 550$ MHz (inset to Fig. 2(c)), while the mechanical mode had $\gamma_m/2\pi \approx 63$ kHz. We fit each normalized reflection spectrum using the theory presented in Ref. 5, where the normalized amplitude reflection coefficient $r(\Delta_{pc})$ is given as:

$$r(\Delta_{pc}) = \frac{1}{1 + \frac{2i(\Delta_{oc} - \Delta_{pc})}{\kappa} + \frac{C}{\frac{2i(\omega_m - \Delta_{pc})}{\gamma_m} + 1}} \quad (1)$$

$R(\Delta_{pc}) = |r|^2$ is the normalized reflected intensity, and in the limit of $\Delta_{oc} = \omega_m$, $\Delta R = 1 - 1/(1 + C)^2$. The contrast in the EIT dip, $\Delta R = 1 - R(\Delta_{pc} = \omega_m)$, is then plotted as a function of control field power in Fig. 2(c). Recalling that $C = \frac{4Ng_0^2}{\kappa\gamma_m}$, we use Eq. (1) in a fit to extract $g_0/2\pi \approx 7.8$ kHz, where knowledge of the FTW loss, cavity mode transmission spectrum, and Δ_{oc} allows us to estimate N at each pump power [19]. We see good agreement between experiment and theory, further supported by the linear increase in EIT dip width with pump power (lower inset to Fig. 2(c)). However, the experimentally determined g_0 is nearly two times smaller than that predicted from finite element simulations ($g_0/2\pi \approx 15$ kHz) that exclusively consider the contribution due to moving dielectric boundaries. A study of whether photo-elastic

effects may play a role [24] in this discrepancy is underway. Finally, shifting the control field to the blue-detuned side of the optical mode ($\Delta_{oc} \approx -\omega_m$) results in electromagnetically induced absorption (EIA), evidenced by a peak in the center of the reflection spectrum that increases with optical power (Fig. 2(d)).

Whispering gallery mode cavities can support high- Q optical modes over a broad range of wavelengths. As a result, multiple, broadly spaced optical modes may be expected to couple to the same mechanical mode, which we observe in our measurements. Figure 2(e)-(g) presents EIT and EIA data for a 980 nm band optical mode ($\kappa/2\pi \approx 750$ MHz) that couples to the 625 MHz radial breathing mode. We observe similar behavior as seen for the 1300 nm band mode, though the maximum contrast of the EIT dip and EIA peak are a little smaller, likely due to lower Q_o which is not fully compensated by higher optical power before thermal instability sets in.

One application of multiple optical modes coupled to the same mechanical mode is in wavelength conversion, as outlined in theory [12] and recently demonstrated in silicon optomechanical crystals [13] and silica microspheres [14]. The application of two control fields, each red-detuned from an optical mode by ω_m , opens up a pair of transparency windows over which wavelength conversion, mediated by the mechanical resonator, can occur. Input signals over a bandwidth set by the damped mechanical resonator can be upconverted or downconverted, with an internal conversion efficiency that depends on the cooperativity achieved for each optical mode.

We proceed following the recent experiments of Hill et al. [13], as shown in the setup in Fig. 3(a). RF switches are used to alternate between EIT spectroscopy on the

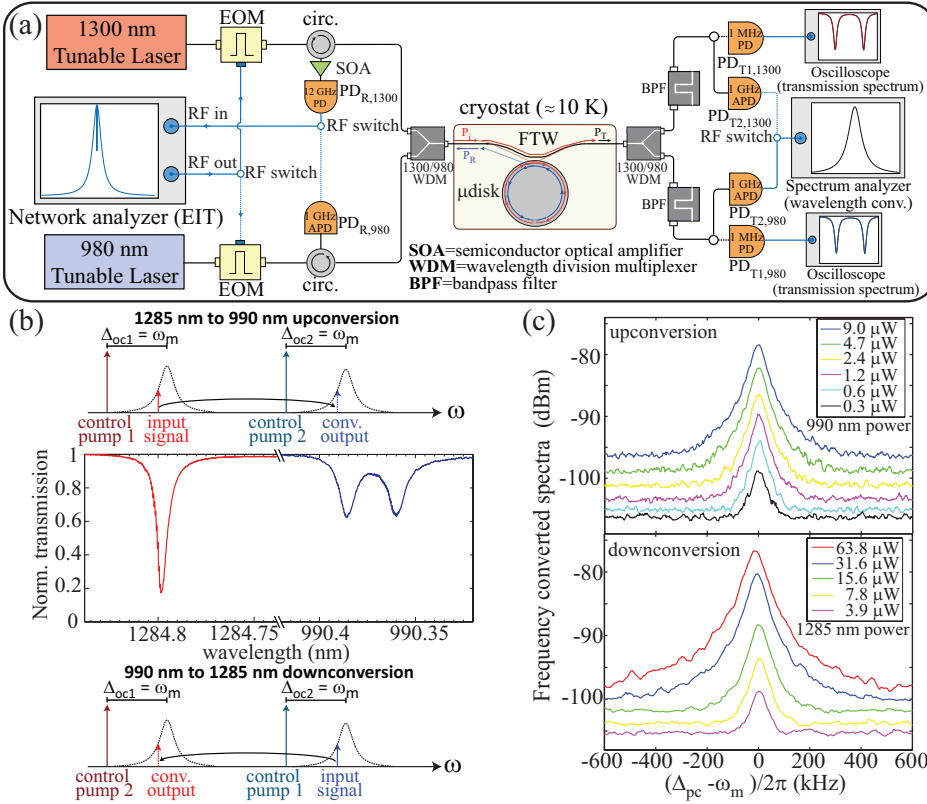


FIG. 3. Wide-band wavelength conversion experiment: (a)-(b) Experimental schematics. As in Fig. 1(a), EIT spectroscopy in the 1300 nm and 980 nm bands is performed on the reflected signal from the cavity, with fast switching between the two bands enabled by RF switches. In frequency upconversion (downconversion), the 1300 nm (980 nm) laser is modulated to generate an input probe field, which is converted to the 980 nm (1300 nm) band through application of the 980 nm (1300 nm) control field. The frequency converted field transmitted past the cavity is measured on the spectrum analyzer. Along with schematics, part (b) shows the optical mode transmission spectra for the measured device. (c) Up-converted (top) and downconverted (bottom) signals measured by the spectrum analyzer, measured as the relevant probe-control field detuning (Δ_{pc}) is swept and the 990 nm (top) or 1300 nm (bottom) control field power is stepped.

reflected signal from the cavity in the 1300 nm band and in the 980 nm band. These EIT measurements are done to ascertain Δ_{oc} for each mode, as well as the cooperativity achieved. For the experiments that follow, $\Delta_{oc} \approx \omega_m$ for both control fields. Focusing first on frequency upconversion, we amplitude modulate the 1300 nm laser to generate an input probe signal that is detuned from the control field by Δ_{pc} . The control field and input probe signal in the 1300 nm band are combined with the control field in the 980 nm band using a wavelength division multiplexer (WDM), and sent into the FTW-coupled microdisk. Light exiting the device is separated into the 980 nm and 1300 nm bands using a WDM and bandpass filters (BPFs). Since the converted tone in the 980 nm band is detuned with respect to the 980 nm band control field by Δ_{oc} , the beating of the two fields is recorded on an electronic spectrum analyzer after detection by a 1 GHz APD. The input probe-control field detuning Δ_{pc} is then swept in order to assess the conversion bandwidth. For frequency downconversion, the roles of the 980 nm band and 1300 nm band lasers are reversed (Fig. 3(b)).

Figure 3(b) shows the optical transmission spectrum for modes in the 1300 nm and 980 nm bands. In comparison to the data from Fig. 1 and 2, the Q_o here are lower, with $\kappa/2\pi \approx 1$ GHz and 3 GHz in the 1300 nm and 980 nm bands, respectively. The increased losses are both due to additional sample degradation and the need to simultaneously achieve a reasonable coupling level to both optical modes (in Fig. 2, this was individually op-

timized). Figure 3(c) shows a series of converted spectra for frequency upconversion (top) and downconversion (bottom), where each trace is acquired as Δ_{pc} is swept. For upconversion (downconversion), the 1300 nm (980 nm) control field power is held fixed, while the 980 nm (1300 nm) control field power is stepped. Both graphs show an increase in the converted signal strength with control field power, though internal (external) conversion efficiencies [19] are limited to $\approx 20.9\%$ (0.63%).

The maximum expected internal conversion efficiency is estimated from the cooperativities of the two modes, C_1 and C_2 [13, 14], as $\eta = 4C_1C_2/(1 + C_1 + C_2)^2$. While in Fig. 2, $C_1=C_2=0.45$ was reached, corresponding to a maximum $\eta = 22\%$, the lower Q_o s measured here caused a reduction in C_1 and C_2 that was not fully compensated by additional optical power, thus explaining the lower efficiency. The external conversion efficiency of 0.63% is given by the product of the internal efficiency and the waveguide-cavity incoupling and outcoupling efficiencies, which are 29.2% and 10.3% , respectively.

Eventually, one might envision using such wavelength conversion in connecting quantum optical technology at wavelengths below 1000 nm (e.g., quantum memories, Si single photon counters) and at 1300 nm (low loss/dispersion optical fibers). Several improvements must be made for such quantum frequency conversion [25] to be feasible. As already described, higher cooperativities and more efficient waveguide-cavity coupling are needed to improve the conversion efficiency. The gen-

eration of noise photons is also a crucial consideration for applications such as frequency conversion of single photon states [26], and has contributions that stem from the limited sideband resolution of the system (e.g., from Stokes scattered photons) and the thermal occupancy of the mechanical resonator ($\langle n \rangle_{\text{th}} \approx 330$ for the mechanical mode at 10 K; laser cooling in our experiments reduces this by at most $\approx 33\%$). In contrast, recent work in optomechanical crystals [13] cooled the system close to the ground state ($\langle n \rangle_{\text{th}} \approx 3$), whereas experiments done at room temperature in microspheres [14] have an even larger noise contribution ($\langle n \rangle_{\text{th}} \approx 4 \times 10^4$).

Reduced mechanical damping is one key to improved device performance. While $Q_m \gtrsim 10^6$ has been demonstrated for MHz frequency modes in Si_3N_4 [27], to our knowledge, such Q s have not yet been shown at near-GHz frequencies. Recently, a frequency- Q_m product of 2×10^{13} Hz was demonstrated at room temperature for 10 MHz modes of Si_3N_4 membranes [28]; our corresponding value is 6×10^{12} Hz, suggesting that improved Q_m may be possible. As simulations (Fig. 1(e)) indicate that coupling to pedestal modes may be a limitation on Q_m , smaller pedestal diameters or adjusting the geometry to isolate the periphery of the disk from a central, pedestal-supported region [21] may provide improvements.

Si_3N_4 devices may benefit by supporting a large intracavity photon number N without nonlinear loss which, for example, influences Si optomechanical crystals at $N \gtrsim 300$ [3]. We are able to reach $N \approx 6 \times 10^4$, and further increases are not limited by nonlinear loss, but instead the thermal stability of the device. Techniques to lock Δ_{oc} beyond the simple (and relatively slow) procedure we have adopted [19] would be of significant benefit. Finally, we note that increased g_0 could dramatically improve performance, given the squared dependence of the cooperativity on this parameter. While large increases in g_0 are unlikely for our microdisks, since further decreases in diameter will begin to result in radiation losses, recent designs of Si_3N_4 slot mode optomechanical crystals [29] suggest that such a system may be able to combine high frequency, large g_0 , and large N .

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SUPPLEMENTAL INFORMATION

FINITE ELEMENT SIMULATIONS

We performed finite element method simulations of our microdisk structures to gain a clearer physical understanding of the optomechanical system.

Obtaining optical and mechanical cavity modes

Our microdisk cavities support whispering-gallery optical modes (WGMs) of the form $\mathbf{E}(r, z) \exp(im\phi)$, where $\mathbf{E}(r)$ is the electric field distribution on the rz plane (in cylindrical spatial coordinates) and m is the azimuthal order. Such WGMs were calculated by solving the 2D axially-symmetric electromagnetic wave equation

$$\nabla \times \nabla \times \mathbf{E} = \epsilon(\mathbf{r}) \left(\frac{\omega}{c}\right)^2 \mathbf{E}. \quad (2)$$

via the finite element method, with a formulation that employed respectively edge and node elements for the transverse and longitudinal electric field components, and perfectly-matched layers to simulate open boundaries. Solving the eigenvalue problem in eq. (2) for a specific azimuthal order m produced eigenmodes with complex frequencies ω_m and optical quality factors $Q_m = \text{Re}\{\omega_m\}/(2\text{Im}\{\omega_m\})$. Because WGM fields are mostly concentrated in the periphery of the resonator, interaction with the Si pedestal that supports the SiN microdisk is negligible, and thus completely ignored in the optical mode calculation.

For disk radius $R \approx 5 \mu\text{m}$ and SiN thickness $t \approx 350 \text{ nm}$, modes with radiation-limited quality factors exceeding 10^8 can be found both in the 980 nm and 1300 nm bands. Table I shows wavelengths and quality factors of the calculated TE and TM polarized WGMs, which correspond well with. The good agreement between the experimental and calculated values was achieved by tuning the parameters of the cavity within reasonable bounds (thickness $t = 340 \text{ nm}$ and $n = 1.99$ for the refractive index of SiN), compared to experimentally determined values.

The mechanical modes of the microdisk structure were obtained by solving the equation of motion for the displacement field $\mathbf{Q}(\mathbf{r})$, assuming anisotropic materials [10]. In our simulations, the Si pedestal supporting the SiN microdisk was represented by a conical frustum

TABLE I. Calculated and experimental whispering gallery modes

λ_{FEM} (nm)	$Q_{\text{o,FEM}} \times 10^8$	Polarization	$\lambda_{\text{exp.}}$ (nm)
971.28	10	TE	970
987.37	4.5	TE	984
975.36	5.7	TM	974
989.61	2.4	TE	990
1281.23	1.0	TE	1280
1309.04	0.5	TE	1308

whose angle and height were equivalent to those determined from scanning electron microscope images of fabricated structures. A zero displacement boundary condition was enforced at the bottom surface of the conical frustum, corresponding to the region where the pedestal meets the Si substrate.

For the $10 \mu\text{m}$ diameter disks considered, a first-order radial breathing mode (RBM) is obtained in the vicinity of $f_m = 625 \text{ MHz}$. The displacement profile of the RBM, as shown at the bottom of Fig. 1(e) (mode ③), is primarily in the radial direction and confined to the disk plane, with relatively small vertical displacement in the disk-pedestal contact area. Due to its azimuthal symmetry, the RBM is expected to display preferential optomechanical coupling to the microdisk's WGMs.

Optomechanical coupling

The shift in the frequency f_o of a particular optical resonance due to displacement of the nanostructure boundaries produced by a mechanical resonance at frequency f_m is quantified by the optomechanical coupling $g_{om} = \partial\omega_o/\partial x = \omega_o/L_{\text{OM}}$; here, x is the cavity boundary displacement, $\omega_o = 2\pi f_o$ and L_{OM} is an effective optomechanical interaction length [10]. The effective length L_{OM} can be estimated via the perturbative expression

$$L_{\text{OM}} = \frac{2 \int dV \epsilon |\mathbf{E}|^2}{\int dA (\mathbf{Q} \cdot \mathbf{n}) \left(\Delta\epsilon |\mathbf{E}_{\parallel}|^2 - \Delta(\epsilon^{-1}) |\mathbf{D}_{\perp}|^2 \right)}. \quad (3)$$

Here, $\mathbf{E}$ and $\mathbf{D}$ are the modal electric and electric displacement fields, respectively, $\Delta\epsilon = \epsilon_{\text{diel.}} - \epsilon_{\text{air}}$, $\Delta(\epsilon^{-1}) = \epsilon_{\text{diel.}}^{-1} - \epsilon_{\text{air}}^{-1}$, and $\epsilon_{\text{diel.},\text{air}}$ are the permittivities of the microdisk material and air. The mass displacement due to the mechanical resonance is given by $\mathbf{Q}$, and the normal surface displacement at the structure boundaries is $\mathbf{Q} \cdot \mathbf{n}$, where $\mathbf{n}$ is the surface normal. The integral in the denominator is performed over the entire surface of the nanostructure.

The optomechanical coupling g_{om} can be converted into a pure coupling rate g between the optical and mechanical resonances: $g_0 = x_{\text{zpf}} \cdot g_{om}$, where $x_{\text{zpf}} = \sqrt{\hbar/2m\omega_m}$ is the zero point fluctuation amplitude for

TABLE II. Optomechanical coupling parameters between 980 nm and 1300 nm TE-polarized WGMs and 625 MHz RBM

λ_o (nm)	$Q_o \times 10^8$	$g_{om}/2\pi$ (GHz/nm)	$g_0/2\pi$ (kHz)	L_{om} (μm)
988.41	4.8	42.7	19.9	7.10
1281.80	1.0	33.2	15.5	7.05

mechanical displacement and m is the motional mass of the mechanical resonance at frequency ω_m . The motional mass can be obtained from the displacement $\mathbf{Q}$ and the nanobeam material density ρ by $m = \rho \int dV \left(\frac{|\mathbf{Q}|}{\max(|\mathbf{Q}|)} \right)^2$ [12].

For the RBM at $f_m \approx 625$ MHz above, $m \approx 60$ pg and $x_{zpf} \approx 0.5$ fm. Table II shows calculated values of L_{om} , g_{om} and the vacuum coupling rate g_0 between the RBM and TE-polarized WGMs in both the 980 nm and 1300 nm bands. The calculated g_{om} values are smaller than those estimated via the expression $g_{OM} = \omega_o/R$, with ω_o the optical mode frequency and R the disk radius, which is commonly employed for the case of large disks. For smaller radius disks such as considered here, optical fields extend considerably into the vacuum regions surrounding the dielectric, resulting in an effective optomechanical length L_{om} larger than the actual physical dimension R , as seen in Table II.

Clamping losses

To estimate mechanical clamping losses of the mechanical resonances, we adopted the method of ref. [21], in which the contact region between the disk and the pedestal is modeled as a membrane that radiates acoustic energy with power

$$P = c\rho\Omega_m^2 \int_A dA |\mathbf{Q}(\mathbf{r}) \cdot \hat{\mathbf{z}}|^2, \quad (4)$$

where ρ is the density of the disk material and c is the speed of sound, Ω_m is the angular frequency of the mechanical resonance and $|\mathbf{Q}(\mathbf{r}) \cdot \hat{\mathbf{z}}|^2$ is the out-of-disk-plane displacement over the contact area A . If W_{mech} is the stored mechanical energy of the resonance, the latter's mechanical quality factor can be estimated as

$$Q_m = \left(\frac{P}{\Omega_m W_{mech}} \right)^{-1}. \quad (5)$$

It is apparent in Fig.1 (e), that, for large top pedestal radius, the mechanical quality factor for the RBM tends to decrease with increasing pedestal radius, a result of the increased contact area through which energy may radiate. At the same time, for a contact areas with radius near 200 nm, the RBM mixes with a secondary ('pedestal') mode that displays a large vertical displacement at the disk center, as observed in the profile of mode

(A). Such mixing is evidenced by an anti-crossing between the green and blue mechanical frequency curves in Fig. 1(e), and by a steep decrease in quality factor in the neighborhood of the anti-crossing. Reduced quality factors in this range are associated with the relatively large vertical displacement of the pedestal mode. For radii below 200 nm the RBM quality factor increases again (green curve in Fig. 1(e)), as the pedestal mode is driven towards lower frequencies.

While the geometrical details of the Si pedestal must be included for an exact determination of the pedestal mode frequencies, we have observed that, generally, smaller pedestal top radii were necessary to ensure that such modes would be out of the range of the RBM. Our highest mechanical quality factors were measured for a pedestal radius of 100 nm, which is essentially the smallest size that we can produce with our current fabrication process.

DEVICE FABRICATION

The device fabrication started with a bare silicon wafer, as shown in Fig. 4. A layer of 350 nm thick stoichiometric Si_3N_4 film was grown by low pressure chemical vapor deposition (LPCVD), with a process-induced internal tensile stress of ≈ 800 MPa, as measured by the wafer bowing method. A 500 nm thick positive-tone electron beam (E-beam) resist was spin-coated on the Si_3N_4 film, followed by E-beam lithography and development in hexyl acetate at 8 °C. The patterns were then transferred into the Si_3N_4 layer by an $\text{O}_2/\text{CHF}_3/\text{Ar}$ inductively-coupled plasma reactive ion etch (RIE). This RIE step apparently leaves a thin layer of SiO_2 on top of the exposed Si surface, preventing any subsequent KOH undercut (Fig. 4(b)). To rectify this, before the e-beam resist was removed, an additional $\text{SF}_6/\text{C}_4\text{F}_8$ inductively-coupled plasma RIE was carried out to remove the SiO_2 layer (as well as some Si), while the residual E-beam resist protected the Si_3N_4 device layer. After resist removal using a stabilized $\text{H}_2\text{SO}_4/\text{H}_2\text{O}_2$ solution, the sample was undercut in a 20 % KOH bath, as this concentration has an etch rate that is relatively insensitive to temperature fluctuations. The KOH etch was performed in two steps to achieve a small ($\lesssim 200$ nm) top pedestal diameter under the microdisk. We started to etch the sample at 40 °C to quickly remove the bulk Si, with periodic inspection of the pedestal size under an optical microscope every 6 to 10 minutes. When the pedestal size was less than 1 μm , the undercut was continued at a temperature of 20 °C to reduce the etch rate. The undercut was stopped every 4 minutes for inspection, until one or more microdisks were completely released (etch rate variations across the chip prevent all devices from being completely released for the same undercut time). The pedestal diameters for the remaining (intact) microdisks were typically $\lesssim 200$ nm, as

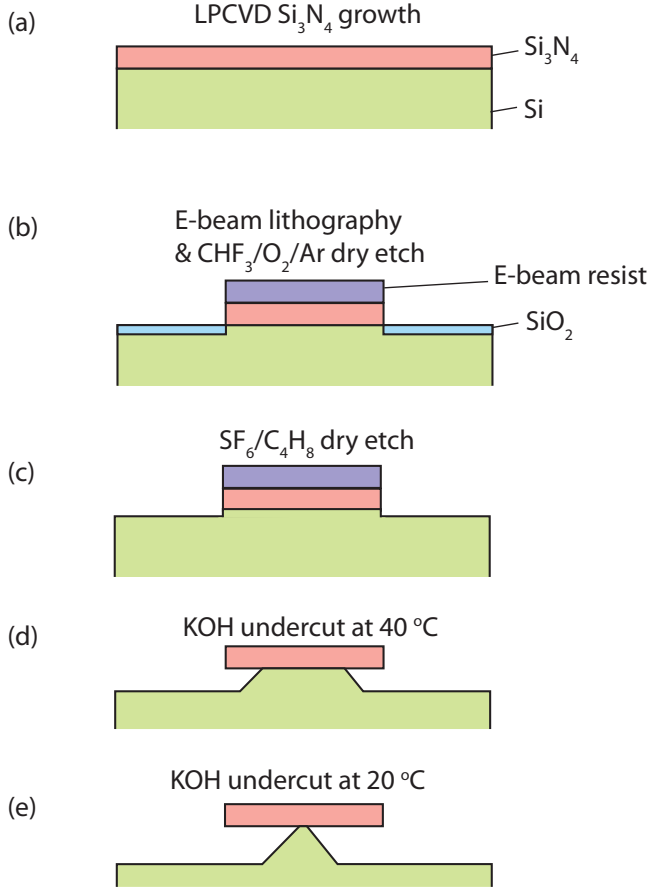


FIG. 4. Processing steps for fabrication of the Si₃N₄ microdisks.

determined by imaging with a scanning electron microscope.

LOCKING OF Δ_{oc}

In EIT experiments, the microdisk cavity is heated when the control laser reaches high power levels, resulting in a red-shift of the resonances due to the thermo-optic effect. It is thus difficult to maintain a fixed detuning (Δ_{oc}) between the control field and optical cavity without feedback. To reduce this instability, we lock Δ_{oc} by adjusting the control laser wavelength to track the red-shifted cavity resonance, following a procedure similar to that outlined in [30]. First, a small portion of the control field is split off and fed to a wavemeter (Fig. 1) equipped with a PID controller whose output is fed back to the laser to fix its absolute wavelength at a specified value. This specified value is determined by sweeping Δ_{pc} over a broad frequency range (0 to 3 GHz) and fitting the acquired data by the vector network analyzer to determine the real value of Δ_{oc} . The control field wavelength is then adjusted to ensure that the desired Δ_{oc} is achieved, and the process repeated until the fit value of Δ_{oc} remains

stable over several scans in a row. Typical locking times are on the order of a few seconds (for lower powers) up to a couple tens of seconds (for the highest powers). Power levels beyond that shown in Fig. 2 result in thermally unstable behavior, where the cavity mode shifts too far away from the control laser for the above approach to be effectively applied.

Once the locking procedure kept Δ_{oc} within a predetermined acceptable range around the target value (e.g., 50 MHz), EIT measurements consist of sweeps of Δ_{pc} recorded over two frequency ranges - the first over a broad range to provide an overall picture of the cavity reflection spectrum, and the second over a narrow range to record the details of the EIT dip. For each set of parameters (optical powers and Δ_{oc}), these sweeps were repeated 16 times and the data plotted in Fig. 2 is an average of these scans.

FITTING THE DATA

Experimentally-measured optical transmission spectra are fit using coupled mode theory for a resonator-waveguide system. For single dips, this yields a Lorentzian function, while doublet modes are fit using a model that takes into account backscattering due to surface roughness, as described elsewhere [31, 32]. In the limit of large doublet splitting with respect to the cavity linewidths, a pair of Lorentzians can accurately fit the data. Mechanical spectra were fit with single Lorentzian functions.

Fitting of the EIT signals (Fig. 2(b)) is based on Eq. (1) from the main text, which we repeat here:

$$r(\Delta_{pc}) = \frac{1}{1 + \frac{2i(\Delta_{oc} - \Delta_{pc})}{\kappa} + \frac{C}{\frac{2i(\omega_m - \Delta_{pc})}{\gamma_m} + 1}} \quad (6)$$

The values of κ , Δ_{pc} , and Δ_{oc} were acquired from the broad scans of the EIT signal. The intracavity photon number is determined as:

$$N = \frac{1}{\hbar\omega_o} \sqrt{\xi} \Delta T Q_i \left(\frac{P_{in}}{\omega_o} \right) \frac{1}{1 + \left(\frac{\Delta_{oc}}{2\kappa} \right)^2} \quad (7)$$

where $\hbar$ is the Planck constant divided by 2π , ξ is the FTW transmission, ΔT is the depth of the optical resonance in the transmission spectrum ($\Delta T=1$ at critical coupling), Q_i the intrinsic optical Q , and P_{in} is the optical power at the FTW input. We measured a background signal with the FTW far away from the device to account for the frequency-dependent response of the APD, EOM, and network analyzer. The fitting was carried out on the experimentally acquired EIT data divided by the background signal.

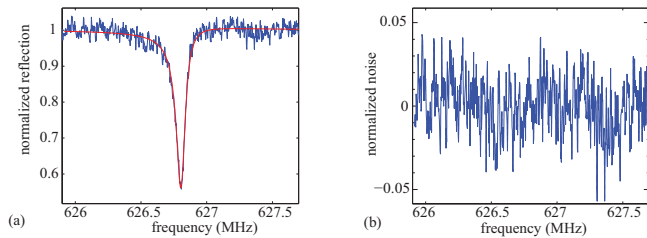


FIG. 5. (a) Raw data (blue) and the fitted curve (red) of the 1300 nm EIT signal at the control power of $21.9 \mu\text{W}$. (b) Difference between the raw data and the fitted curve shown in (a).

The fitting of the EIT width versus control power (inset in Fig. 2(c)) is based on the expression for the total mechanical damping rate $\gamma = \gamma_m(1 + C)$. The fitted value of g_0 from the EIT width is approximate equal to that obtained from the EIT depth fitting, with an error of $\approx 6 \%$.

UNCERTAINTY ESTIMATES

The error bars in Fig. 2(c) arise from the noise of recorded raw EIT data. By subtracting the fitted curve from the raw EIT data (Fig. 5(a)), we obtained the noise of the EIT signal (Fig. 5(b)). The one standard deviation value of this noise signal is considered as the uncertainty of the EIT signal depth and is plotted as the error bar in Fig. 2(c). By combining the uncertainty of the reflected EIT signal and the slopes of the fitted curves at both the left and right shoulders, we obtained the uncertainty of the width of the EIT signal. This width uncertainty is plotted as the error bars in the inset figure of EIT width versus the optical power in Fig. 2(c).

The uncertainty in Q_m shown in Fig. 1(d) is given by the 95 % confidence intervals of the Lorentzian curve fitting of the experimentally measured mechanical spectra.